

### **REMARKS**

At the outset, the Examiner is thanked for the thorough review and consideration of the subject application. The Office Action of June 10, 2003 has been received and its contents carefully reviewed. In addition, Applicant wishes to thank the Examiner for the courtesies extended to the Applicant's representatives during the personal interview conducted on September 4, 2003. During the personal interview, Applicant noted that the test devices used in Cristoloveanu et al. do not have a transistor structure.

By this Amendment, Applicant amends claims 1, 14, 25, and 37. No new matter has been added. Accordingly, claims 1-37 are currently pending in the present application. Reexamination and reconsideration of the application in view of the above amendments and the following remarks are respectfully requested.

In the Office Action, the proposed drawing changes that were previously filed on April 11, 2003 are disapproved because the changes were not in the form of "pen-and-ink sketch showing changes in red ink or with the changes highlighted." Applicant resubmits the proposed drawing changes in FIGS. 1A-3D and 4C to include "Related Art" in the legend of each figure, as indicated in red in the attached Annotated Sheets Showing Changes. Also, Applicant wishes to clarify the statement to insert element number 45 by stating element number 45, as indicated in red in the attached Annotated Sheets Showing Changes, is added to identify the nickel thin film that is illustrated as being deposited over the source 41S and drain 41D and the gate electrode 43. Reconsideration of the proposed drawing changes is requested.

In the Office Action, the Examiner rejected claims 1-37 under 35 U.S.C. § 103, as being unpatentable over the combination of Maekawa (US Patent No. 6,066,547), Arai et al. (US Patent No. 5,576,222) and Seung-Ik Jun (Aepse '97) and/or Cristoloveanu et al. (SOI). The Office Action states that the claims of the present application are "made obvious by the combination of Maekawa, Arai et al., Seung Ik Jun and Cristoloveanu et al. would inherently possess the recited off current because the same materials are treated in the same manner as in the instant invention"(Office Action, page 2). Applicant traverses the rejection below.

Applicant respectfully submits claims 1, 25 and 37 are allowable over the cited references in that claims 1, 25 and 37 recite a method of fabricating a thin film transistor for a

liquid crystal display having a plurality of pixels that includes, among other features, “wherein the thin film transistor includes source and drain regions and channel region, and wherein the amorphous silicon layers in the source and drain regions are crystallized by MIC and the amorphous silicon layer in the channel region is crystallized by FALC during the application of the thermal treatment and electric field, whereby the amorphous silicon layer in the channel region is substantially free from metal atoms of the metal layer.” None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, claims 1, 25 and 37 and claims 2-13 and 26-36, which depend therefrom, are allowable over the cited references.

Applicant further submits claim 14 is allowable over the cited references in that claim 14 recites a method of fabricating a thin film transistor for a liquid crystal display having a plurality of pixels that includes, among other features, “wherein the thin film transistor includes source and drain regions and channel region, and wherein the first amorphous silicon layers in the source and drain regions are crystallized by MIC and the first amorphous silicon layer in the channel region is crystallized by FALC during the application of the thermal treatment and electric field, whereby the first amorphous silicon layer in the channel region is substantially free from metal atoms of the metal layer.” None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 14, and claims 15-24, which depend therefrom, are allowable over the cited references.

Applicant believes the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited. If the Examiner deems that a telephone conference would further the prosecution of this application, the Examiner is invited to call the undersigned attorney at the telephone number (202) 496 - 7500. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Dated: October 10, 2003

Respectfully submitted,

By 

Rebecca Goldman Rudich

Registration No.: 41,786

MCKENNA LONG & ALDRIDGE LLP

1900 K Street, N.W.

Washington, DC 20006

(202) 496-7500

Attorney for Applicant



30827

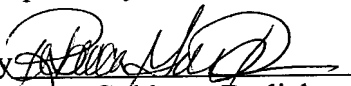
PATENT TRADEMARK OFFICE

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Dated: October 10, 2003

Respectfully submitted,

By

  
Rebecca Goldman Rudich

Registration No.: 41,786

MCKENNA LONG & ALDRIDGE LLP

1900 K Street, N.W.

Washington, DC 20006

(202) 496-7500

Attorney for Applicant



30827

PATENT TRADEMARK OFFICE

RECEIVED  
OCT 21 2003  
TECHNOLOGY CENTER 2800



Appln. No. 09/170,625  
Amdt. Dated 10/10/03  
Reply to Office Action of 6/10/03  
Annotated Sheet Showing Changes

FIG .1A -- Related Art --

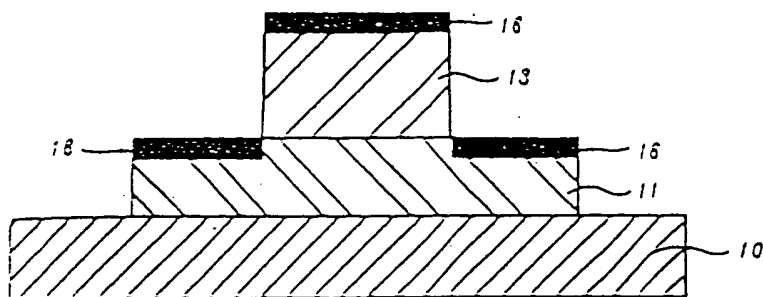
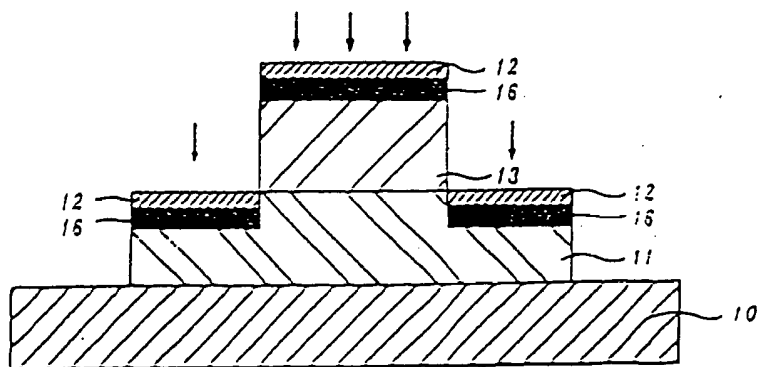


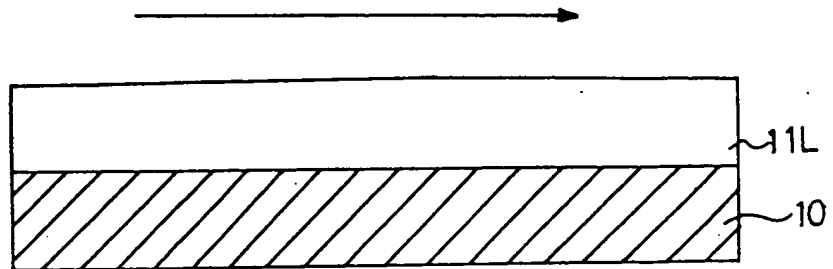
FIG .1B -- Related Art --





Appln. No. 09/170,625  
Amdt. Dated 10/10/03  
Reply to Office Action of 6/10/03  
Annotated Sheet Showing Changes

FIG .2 -- Related Art --





Appln. No. 09/170,625  
Amdt. Dated 10/10/03  
Reply to Office Action of 6/10/03  
Annotated Sheet Showing Changes

FIG .3A --Related Art--

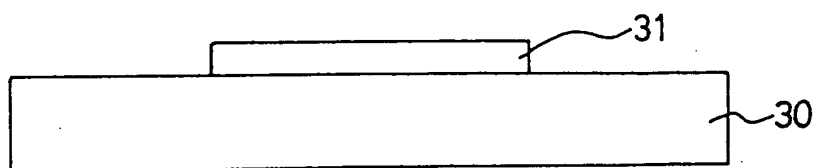
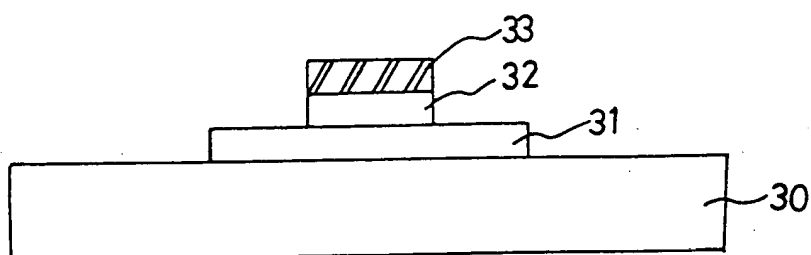


FIG .3B --Related Art--





Appln. No. 09/170,625  
Amdt. Dated 10/10/03  
Reply to Office Action of 6/10/03  
Annotated Sheet Showing Changes

FIG .3C -- Related Art --

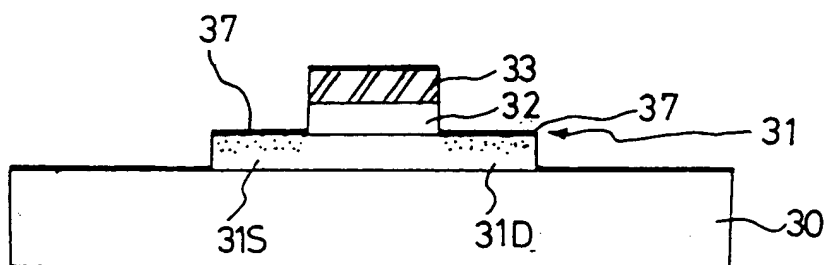


FIG .3D -- Related Art --

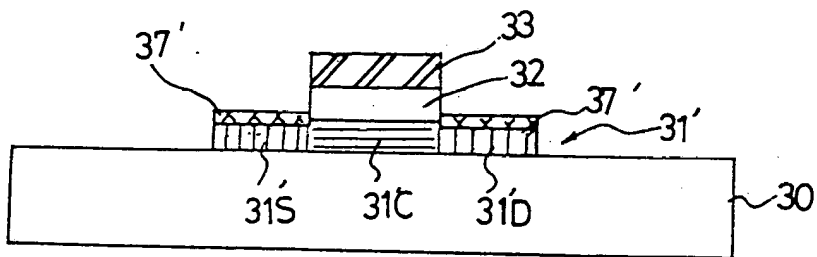






FIG .4A

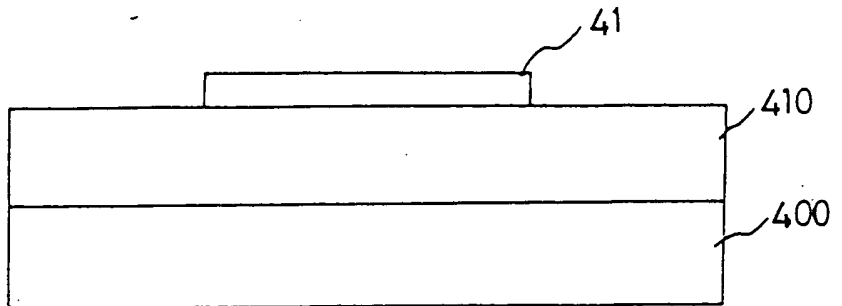


FIG .4B

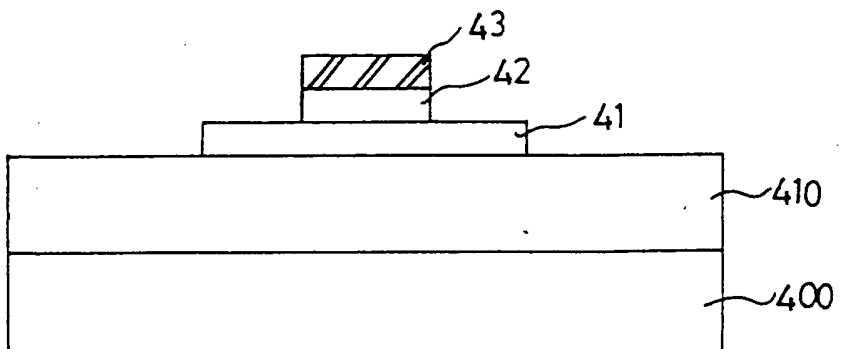
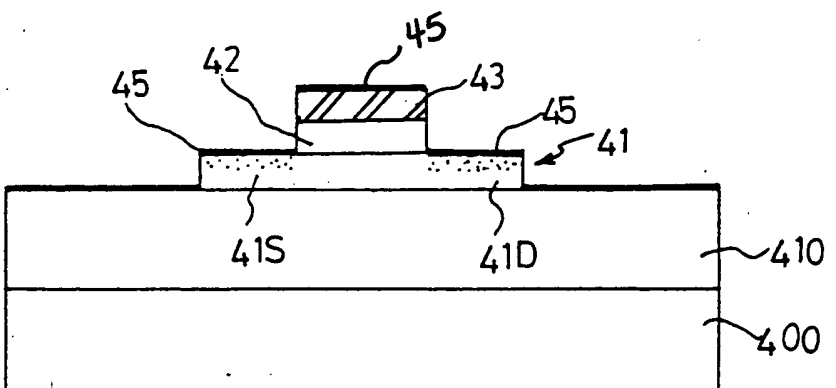
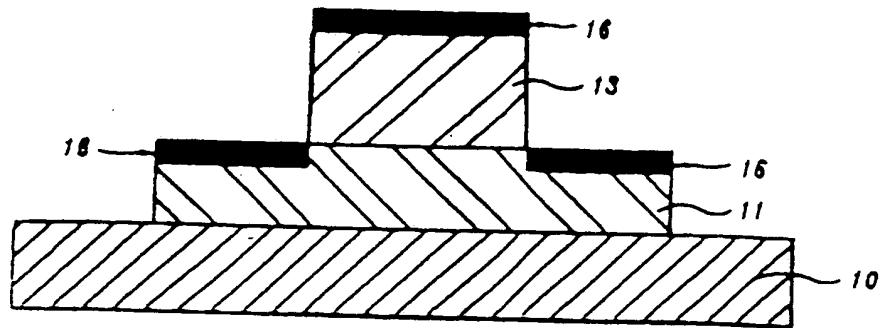


FIG .4C

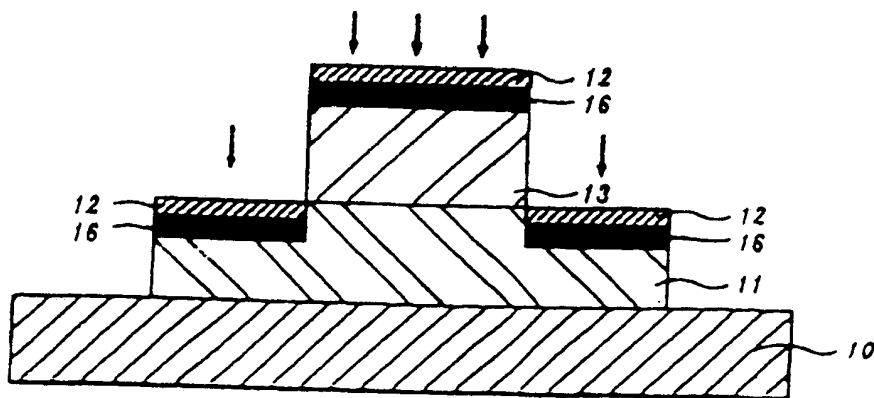




**FIG. 1A** Related Art



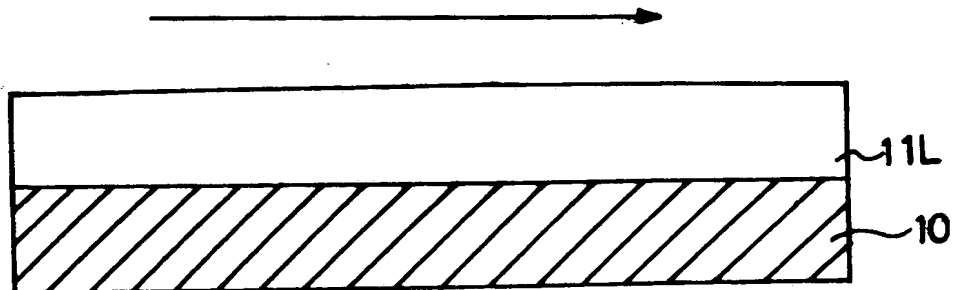
**FIG. 1B** Related Art





Appln. No. 09/170,625  
Amdt. Dated 10/10/03  
Reply to Office Action of 6/10/03  
Renlacement Sheet

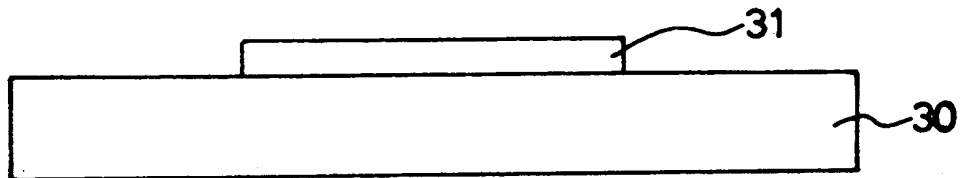
**FIG. 2** Related Art



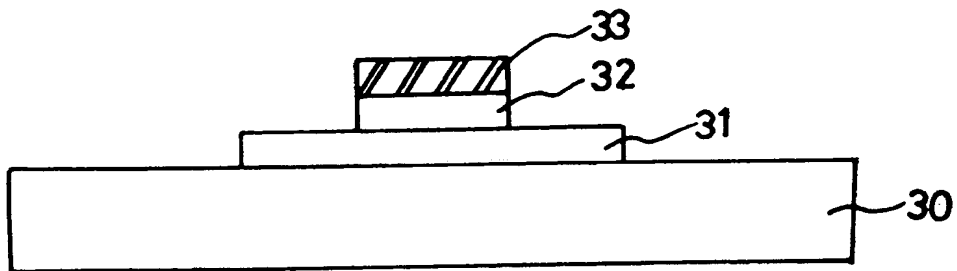
2  
OCT 14 2003  
PATENT & TRADEMARK OFFICE

Appln. No. 09/170,625  
Amdt. Dated 10/10/03  
Reply to Office Action of 6/10/03  
Replacement Sheet

**FIG. 3A** Related Art

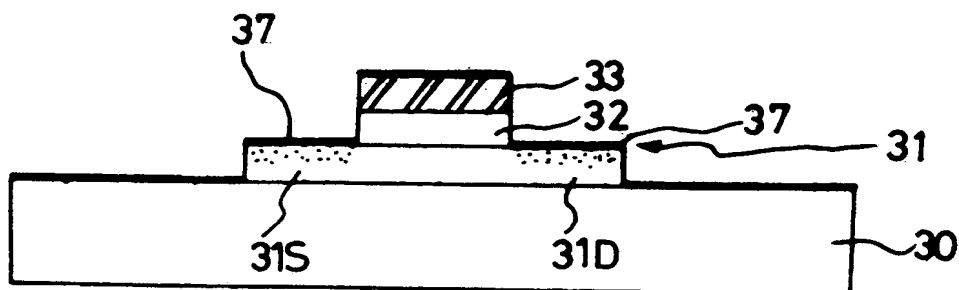


**FIG. 3B** Related Art

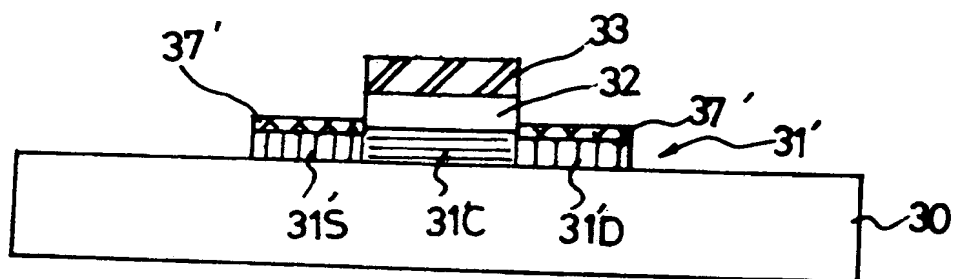




**FIG. 3C** Related Art



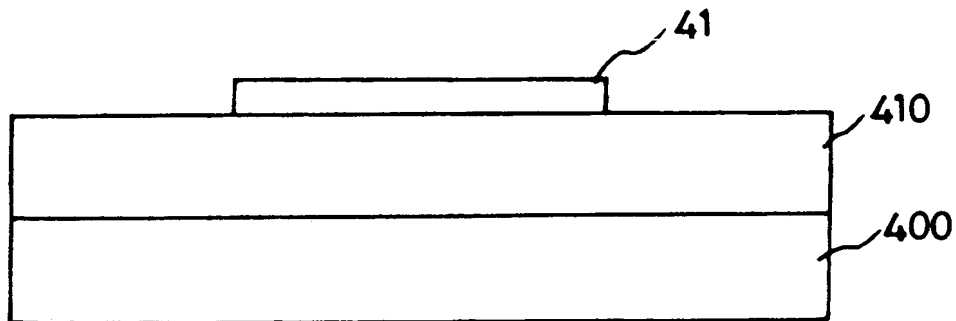
**FIG. 3D** Related Art



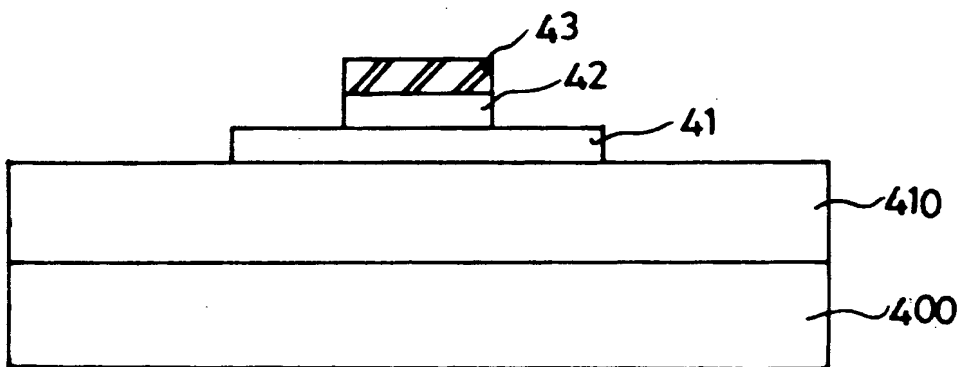


10/10/03

**FIG. 4A**



**FIG. 4B**



**FIG. 4C**

